

INFORMATION DISCLOSURE CITATION IN AN APPLICATION (PTO-1449)				ATTY. DOCKET NO. 61352-051		SERIAL NO. 10/687,647	
				APPLICANT Yoshiaki HASEGAWA, et al.			
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U.S. PATENT DOCUMENTS							
EXAMINER'S INITIALS	CITE NO.	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear		
26		US 5,757,833	05/26/1998	Arakawa et al.	Corresponds to JP 9-191150		
		US					
		US					
		US					
FOREIGN PATENT DOCUMENTS							
EXAMINER'S INITIALS	CITE NO.	Foreign Patent Document Country Code-Number + Kind Codes (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Figures Appear	Translation	
						Yes	No
26		JP P2001-244560A	09/07/2001	SONY CORP		(Japan w/English Abstract)	
		JP P2000-196188A	07/14/2000	TOSHIBA CORP		(Japan w/English Abstract)	
		JP 9-191150	07/22/1997		Corresponds to US 5,757,833		
		JP 63-1370	01/07/1988	SANYO ELECTRIC CO., LTD.		(Front page of Japanese Patent and English Abstract)	
		JP 63-34992	02/15/1988	NEC CORP		(Japan w/English Abstract)	
		JP 5-343813	12/24/1993	ASAHI GLASS CO LTD		(Japan w/English Abstract)	
W		JP 5-259079	10/08/1993	NEC CORP		(Japan w/English Abstract)	
OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)							
EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.					
26		Shuji NAKAMURA, "InGaN Multiquantum-Well-Structure Laser Diodes with GaN-AlGaIn Modulation-Doped Strained-Layer Superlattices", IEEE Journal of Selected Topics in Quantum Electronics, Vol. 4, No. 3, May/June 1998, p. 483-489					
		H. MARCHAND, et al., "Mechanisms of Lateral Epitaxial Overgrowth of Gallium Nitride by Metalorganic Chemical Vapor Deposition", Journal of Crystal Growth, 195 (1998) 328-332					
		Michael KNEISSL, et al., "Performance and Degradation of Continuous-wave InGaIn Multiple-Quantum-Well Laser Diodes on Epitaxially Laterally Overgrown GaN Substrates", Applied Physics Letters, Vol. 77, No. 13, September 25, 2000, pages 1931-1933					
		Shuji NAKAMURA, "UV/Blue/Green InGaIn-Based LEDs and Laser Diodes Grown on Epitaxially Laterally Overgrown GaN", IEICE Trans. Electron., Vol. E83-C, No. 4, April 2000, p. 529-535					
26		Shuji NAKAMURA, et al., "InGaIn/GaN/AlGaIn-Based Laser Diodes with Modulation-Doped Strained-Layer Superlattices Grown on an Epitaxially Laterally Overgrown GaN Substrate", Applied Physics Letters, Vol. 72, No. 2, pages 211-213 (1998)					
EXAMINER H. P. KAMANT				DATE CONSIDERED 12/08/04			

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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